

Andrew S. Grove

Articles



[Wired Magazine, June 2001](#)

[Andy Grove's Rational Exuberance](#)

Boom and bust have always been strictly business for Intel and its fearless leader. No wonder high tech's legendary skeptic is also an Internet bull. Interview by John Heilemann.



[Esquire Magazine, May 2000](#)

[What I've Learned](#)

Intel icon Andy Grove reflects on profits, technology, and the business of living. "Risk is the cost of aggressive objectives." Interview by Mike Sager.



[ETime Magazine, December 1997](#)

[Man of the Year](#)

The microchip is the dynamo of a new economy... driven by the passion of Intel's Andrew Grove.

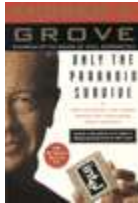
Books



Swimming Across

Combining a child's sense of wonder with an engineer's passion for detail, Andy Grove re-creates a Europe that has since disappeared. Set in the cruel years of Hungary's Nazi occupation and subsequent Communist regime, *Swimming Across* is the stunning childhood memoir of one of the leading thinkers of our time, the legendary Intel Chairman.

Publish date: 2001, by: [Time Warner](#)
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Only the Paranoid Survive

In *Only the Paranoid Survive*, Grove reveals his strategy of focusing on a new way of measuring the nightmare moment every leader dreads - when massive change occurs and a company must, virtually overnight, adapt or fall by the wayside. Grove calls such a moment a Strategic Inflection Point. When a Strategic Inflection Point hits, the ordinary rules of business go out the window.

Publish date: 1999, by: [Time Warner](#)
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High Output Management

Step by step, Andy Grove shows the executive at any level how to use the management techniques perfected at Intel. By applying the *principles of manufacturing* to managerial work, by getting as much *leverage* as possible from the tasks he chooses to perform himself, and by eliciting *peak performance* from subordinates, the manager can bring to the working environment the precise and intense teamwork found in athletic competition.

Publish date: 1995, by: [Random House](#)



One on One With Andy Grove

One-On-One With Andy Grove is packed with expert, sensible, and hard-hitting advice about how to deal with people on the job. From employee-boss resentment to competition among the ranks, from giving praise and placing blame to firing someone the right way, Grove tackles the nitty-gritty issues that crop up in the workplace every day.

[Penguin Putnam Books for Young Readers](#) -- *This book is currently out of print.*



Physics and Technology of Semiconductor Devices

Provides a comprehensive treatment of semiconductor device physics and technology, with emphasis on modern planar silicon devices. Physical principles are explained by the use of simple physical models and illustrated by experimental measurements.

[Wiley Publishers](#)

List of Selected Technical Papers

Semiconductor Technology

F.H. Shair, A.S. Grove, E.E. Petersen and A. Acrivos, "The Effect of Confining Walls on the Stability of the Steady Wake behind a Circular Cylinder", J. of Fl. Mech. 17, 546 (1963)

A.S. Grove, E.E. Petersen and Andreas Acrivos, "Velocity Distribution in the Laminar Wake of a Parallel Flat Plate", Phys. of Fl. 7, No. 7 (1964)

A.S. Grove, F.H. Shair, E.E. Petersen and Andreas Acrivos, "An Experimental Investigation of the Steady Separated Flow Past a Circular Cylinder", J. of Fl. Mech. 19, 60 (1964)

Andreas Acrivos, D.D. Snowden, A.S. Grove and E.E. Petersen, "The Steady Separated Flow Past a Circular Cylinder at Large Reynolds Numbers", J. of Fl. Mech. 21, 737 (1965)

B.E. Deal, A.S. Grove, E.H. Snow and C.T. Sah, "Observation of Impurity Redistribution During Thermal Oxidation of Silicon Using the MOS Structure", J. Electrochem. Soc. 112, 3 (1965)

O. Leistiko, Jr. and A.S. Grove, "Breakdown Voltage of Planar Silicon Junctions", Sol.-St. Elec. 9, 847 (1966)

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E.H. Snow, A.S. Grove, D.J. Fitzgerald, "Effects of Ionizing Radiation on Oxidized Silicon Surfaces and Planar Devices", Proc. of IEEE, 55, 7, 1168 (1967)

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*R.N. Noyce, R.E. Bohn and H.T. Chua, "Schottky Diodes Make IC Scene", Electronics, July 1969

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Andrew S. Grove, "Advances in LSI Technology", Colloque International sur la Microelectronique Avancee (International Conference on Advance Microelectronics), (1970). Also reprinted in Topics in Solid State and Quantum Electronics, 404-419, John Wiley (1972)

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A.S. Grove, C.T. Sah, "Simple Analytical Approximations to the Switching Times in Narrow Base Diodes", Sol. St. Elec. 7, 107 (1964)

A.S. Grove, E.H. Snow, B.E. Deal and C.T. Sah, "Simple Physical Model for the Space-Charge Capacitance of Metal-Oxide-Semiconductor Structures", J. Appl Phys. 35, 8, 2458 (1964)

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A.S. Grove, P. Lamond, et al, "Stable MOS Transistors", Electro-Technology, Dec. 1965

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